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Kind regards,

Team Nexperia

PEMD17; PUMD17

NPN/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 22 k Ω

Rev. 03 — 24 January 2005

Product data sheet

1. Product profile

1.1 General description

NPN/PNP resistor-equipped transistors.

Table 1: Product overview

Type number	Package		PNP/PNP complement	NPN/NPN complement
	Philips	JEITA		
PEMD17	SOT666	-	PEMB17	PEMH17
PUMD17	SOT363	SC-88	PUMB17	PUMH17

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place cost

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replacement of general-purpose transistors in digital applications

1.4 Quick reference data

Table 2: Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
Io	output current (DC)		-	-	100	mA
R1	bias resistor 1 (input)		33	47	61	kΩ
R2/R1	bias resistor ratio		0.37	0.47	0.57	



2. Pinning information

Table 3: Pinning

Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		R1 R2
5	input (base) TR2		TR1
6	output (collector) TR1	1 2 3	
			1 2 3
			006aaa143

3. Ordering information

Table 4: Ordering information

Type number Package			
	Name	Description	Version
PEMD17	'-	plastic surface mounted package; 6 leads	SOT666
PUMD17	SC-88	plastic surface mounted package; 6 leads	SOT363

4. Marking

Table 5: Marking codes

Type number	Marking code [1]
PEMD17	5N
PUMD17	D9*

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

5. Limiting values

Table 6: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor; for the PNP transistor v	vith negative polar	ity		
V_{CBO}	collector-base voltage	open emitter	-	50	V
V _{CEO}	collector-emitter voltage	open base	-	50	V
V _{EBO}	emitter-base voltage	open collector	-	10	V
VI	input voltage TR1				
	positive		-	+40	V
	negative		-	-10	V
VI	input voltage TR2				
	positive		-	+10	V
	negative		-	-40	V
Io	output current (DC)		-	100	mA
I _{CM}	peak collector current		-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT363		[1] -	200	mW
	SOT666		[1] [2] _	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
Per device)				
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT363		<u>[1]</u> -	300	mW
	SOT666		[1] [2] _	300	mW

^[1] Device mounted on a FR4 printed-circuit board, single-sided copper, standard footprint.

^[2] Reflow soldering is the only recommended soldering method.



6. Thermal characteristics

Table 7: Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
R _{th(j-a)}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C				
	SOT363		<u>[1]</u> -	-	625	K/W
	SOT666		[1] [2] _	-	625	K/W
Per device)					
R _{th(j-a)}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C				
	SOT363		<u>[1]</u> -	-	416	K/W
	SOT666		[1] [2] -	-	416	K/W

^[1] Device mounted on a FR4 printed-circuit board, single-sided copper, standard footprint.

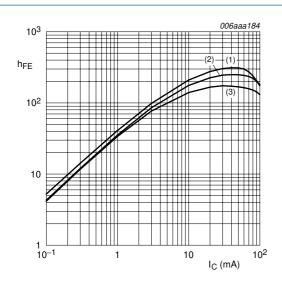
7. Characteristics

Table 8: Characteristics

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor; for the PNP transis	tor with negative polarity				
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	1	μΑ
	cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 \text{ °C}$	-	-	50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	110	μΑ
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	60	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
V _{I(off)}	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	-	1.7	1.2	V
V _{I(on)}	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 2 \text{ mA}$	4	2.7	-	V
R1	bias resistor 1 (input)		33	47	61	kΩ
R2/R1	bias resistor ratio		0.37	0.47	0.57	
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz				
	TR1 (NPN)		-	-	2.5	pF
	TR2 (PNP)		-	-	3	pF

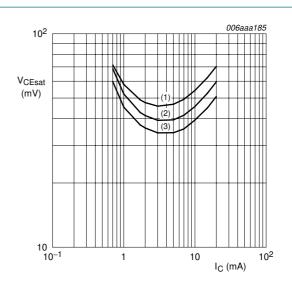
^[2] Reflow soldering is the only recommended soldering method.



$$V_{CE} = 5 V$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \,^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

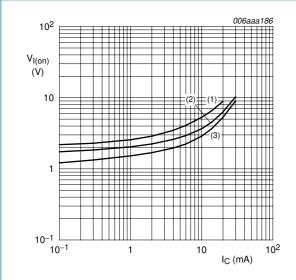
Fig 1. TR1 (NPN): DC current gain as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

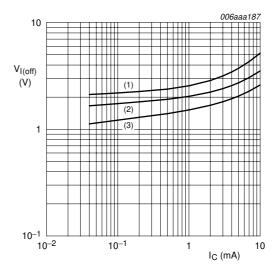
Fig 2. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values





- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \,^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

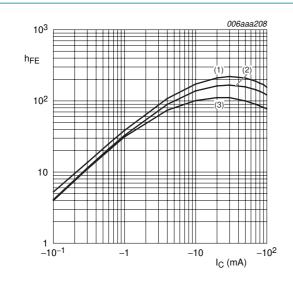
Fig 3. TR1 (NPN): On-state input voltage as a function of collector current; typical values



$$V_{CE} = 5 V$$

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

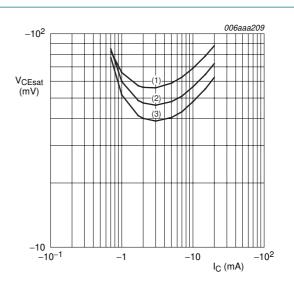
Fig 4. TR1 (NPN): Off-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 \text{ V}$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

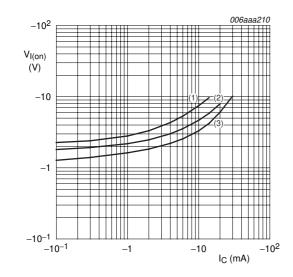
Fig 5. TR2 (PNP): DC current gain as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

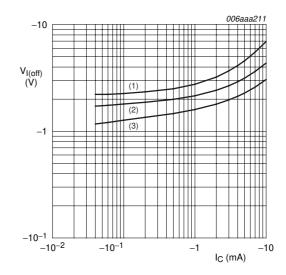
Fig 6. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values





- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 7. TR2 (PNP): On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 \text{ V}$$

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 8. TR2 (PNP): Off-state input voltage as a function of collector current; typical values

8. Package outline

Plastic surface mounted package; 6 leads

SOT363

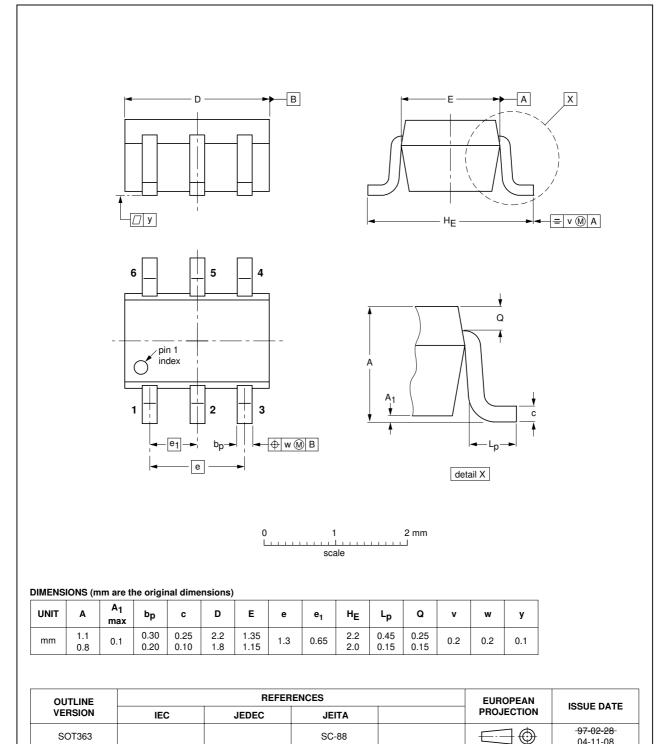


Fig 9. Package outline SOT363 (SC-88)

Plastic surface mounted package; 6 leads

SOT666

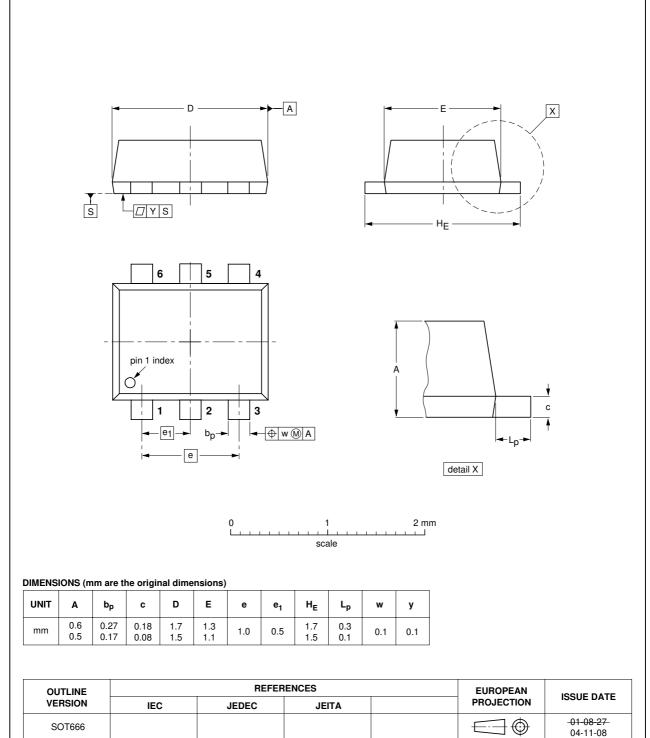


Fig 10. Package outline SOT666

9. Packing information

Table 9: Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description	Packing quantity		
			3000	4000	10000
PEMD17	SOT666	4 mm pitch, 8 mm tape and reel	-	-115	-
PUMD17	SOT363	4 mm pitch, 8 mm tape and reel; T1	115	-	-135
PUMD17	SOT363	4 mm pitch, 8 mm tape and reel; T2	-125	-	-165

^[1] For further information and the availability of packing methods, see Section 14.

^[2] T1: normal taping

^[3] T2: reverse taping

10. Revision history

Table 10: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes	
PEMD17_PUMD17_3	20050124	Product data sheet	-	9397 750 14367	PUMD17_2	
Modifications:	This data s	sheet is an enhanceme	ent of data sheet PU	MD17_2.		
	 The format of this data sheet has been redesigned to comply with the new presentation and information standard of Philips Semiconductors. 					
	Type PEMD17 added					
	 <u>Table 8</u> Characteristics: V_{i(on)} input-on voltage and V_{i(off)} input-off voltage renamed to V_{I(on)} on-state input voltage and V_{I(off)} off-state input voltage 					
	• Figure 1, 2	2, <u>3</u> , <u>4</u> , <u>5</u> , <u>6</u> , <u>7</u> and <u>8</u> ele	ectrical graphs for TI	R1 (NPN) and TR2	(PNP) added	
	• <u>Table 9</u> Pa	cking information adde	ed			
PUMD17_2	20040422	Product specification	-	9397 750 13099	PUMD17_1	
PUMD17_1	20031016	Product specification	-	9397 750 11866	-	

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Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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- [3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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PEMD17; PUMD17

NPN/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 22 k Ω

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